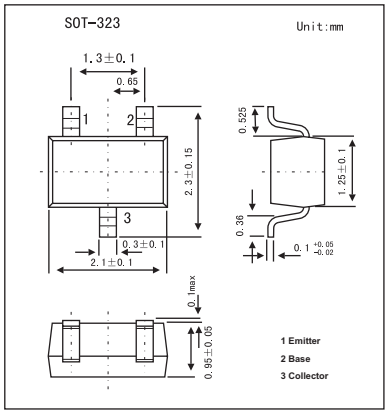
PNP Medium Frequency Transistor

BF824W



Features

- Low current (max. 25 mA).
- Low voltage (max. 30 V).

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-4	V
Collector current	I_C	-25	mA
Peak collector current	I_{CM}	-25	mA
Total power dissipation *	P_{tot}	200	mW
Storage temperature	T_{stg}	-65 to +150	℃
Junction temperature	T_j	150	℃
Operating ambient temperature	R_{amb}	-65 to +150	℃
Thermal resistance from junction to ambient *	$R_{th\ j\text{-}a}$	625	K/W

* Transistor mounted on an FR4 printed-circuit board.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	I_E = 0; V_{CB} = -30 V			-50	nA
		I_E = 0; V_{CB} = -30 V; Tj = 150 ℃			-10	μA
Emitter cutoff current	I_{EBO}	I_C = 0; V_{EB} = -4 V			-100	nA
DC current gain	h_{FE}	I_C = -1 mA; V_{CE} = -10 V	25			
		I_C = -4 mA; V_{CE} = -10 V	25			
Base to emitter voltage	V_{BE}	I_C = -4 mA; V_{CE} = -10 V			-900	mV
Feedback capacitance	C_{rb}	I_C = 0; V_{CE} = -10 V; f = 1 MHz			0.3	pF
Transition frequency	f_T	V_{CE} = -10 V; f = 100 MHz; I_C = -1 mA I_C = -4 mA I_C = -8 mA	250 400 390			MHz

Marking

Marking	F8